

# H7N1004AB

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G1579-0100

Rev.1.00

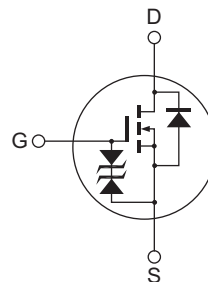
Sep 03, 2007

## Features

- Low on-resistance  
 $R_{DS(on)} = 25 \text{ m}\Omega$  typ.
- Low drive current
- Available for 4.5 V gate drive

## Outline

RENESAS Package code: PRSS0004AC-A  
(Package name: TO-220AB )



1. Gate
2. Drain
3. Source
4. Drain

## Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Drain to source voltage	$V_{DS}$	100	V
Gate to source voltage	$V_{GS}$	$\pm 20$	V
Drain current	$I_D$	30	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	100	A
Body-drain diode reverse drain current	$I_{DR}$	30	A
Avalanche current	$I_{AP}$ <sup>Note2</sup>	15	A
Avalanche energy	$E_{AR}$ <sup>Note2</sup>	22.5	mJ
Channel dissipation	$P_{ch}$ <sup>Note3</sup>	50	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Notes: 1.  $PW \leq 10 \text{ ms}$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_{ch} = 25^\circ\text{C}$ ,  $R_g \geq 50 \Omega$   
 3. Value at  $T_c = 25^\circ\text{C}$

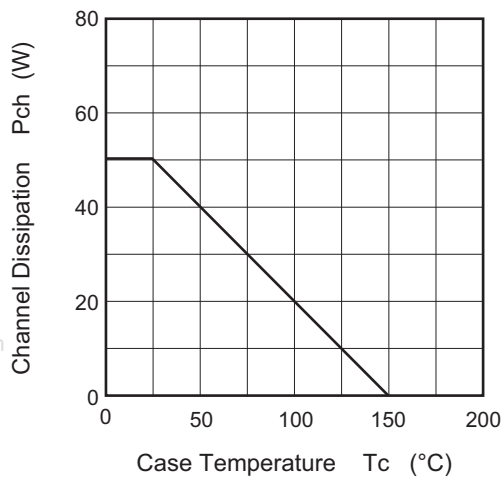
## Electrical Characteristics

(Ta = 25°C)

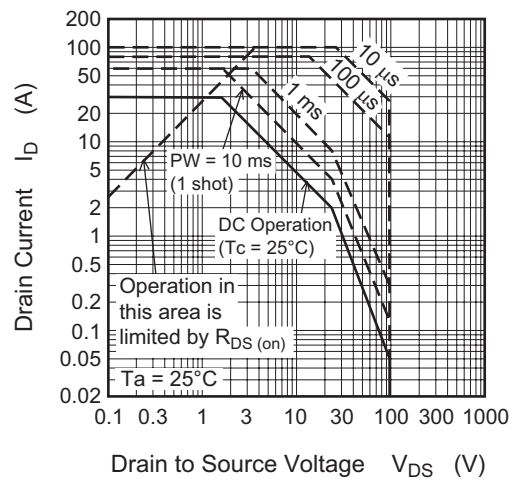
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	$\mu\text{A}$	$V_{DS} = 100 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Static drain to source on state resistance	$R_{DS(on)}$	—	25	35	$\text{m}\Omega$	$I_D = 15 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
		—	30	45	$\text{m}\Omega$	$I_D = 15 \text{ A}$ , $V_{GS} = 4.5 \text{ V}$ <sup>Note4</sup>
Forward transfer admittance	$ y_{fs} $	22	37	—	S	$I_D = 15 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	2800	—	pF	$V_{DS} = 10 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	240	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	140	—	pF	
Total gate charge	$Q_g$	—	50	—	nC	$V_{DD} = 50 \text{ V}$ $V_{GS} = 10 \text{ V}$ $I_D = 30 \text{ A}$
Gate to source charge	$Q_{gs}$	—	9	—	nC	
Gate to drain charge	$Q_{gd}$	—	11	—	nC	
Turn-on delay time	$t_{d(on)}$	—	23	—	ns	$V_{GS} = 10 \text{ V}$ , $I_D = 15 \text{ A}$ $R_L = 2 \Omega$ $R_g = 4.7 \Omega$
Rise time	$t_r$	—	120	—	ns	
Turn-off delay time	$t_{d(off)}$	—	70	—	ns	
Fall time	$t_f$	—	9.5	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	0.9	—	V	$I_F = 30 \text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	47	—	ns	$I_F = 30 \text{ A}$ , $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

## Main Characteristics

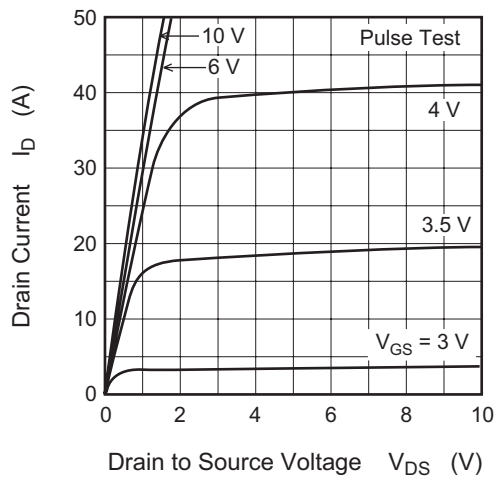
Power vs. Temperature Derating



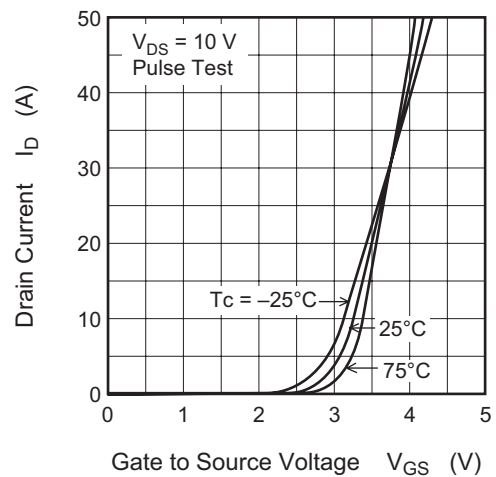
Maximum Safe Operation Area



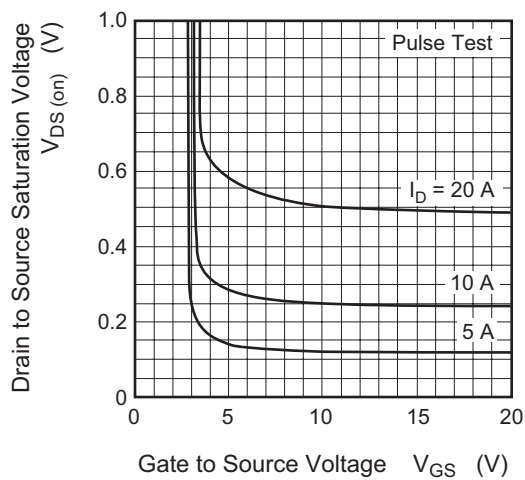
Typical Output Characteristics



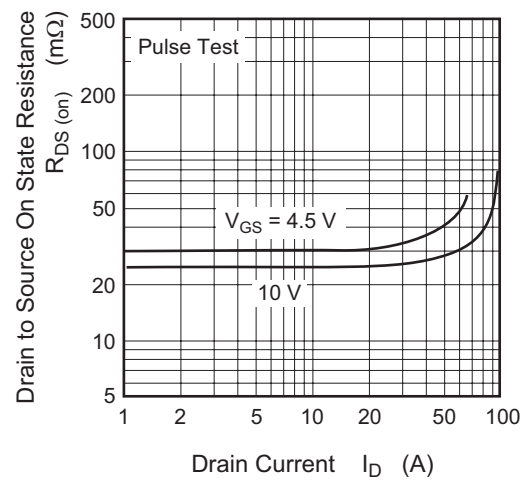
Typical Transfer Characteristics

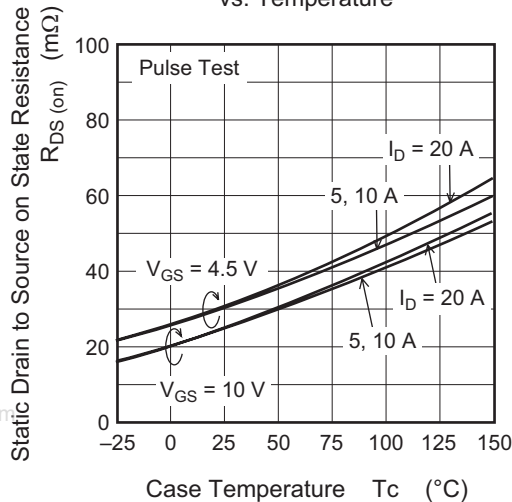
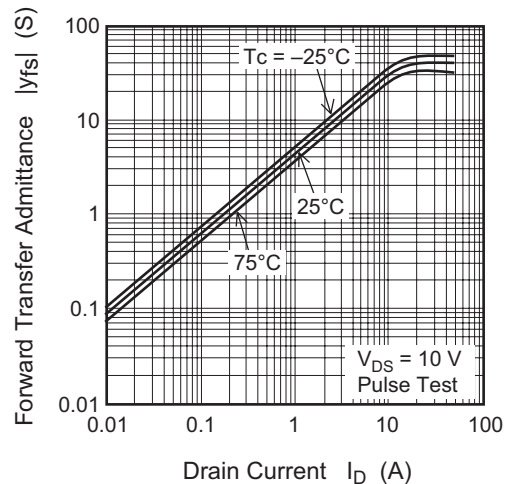
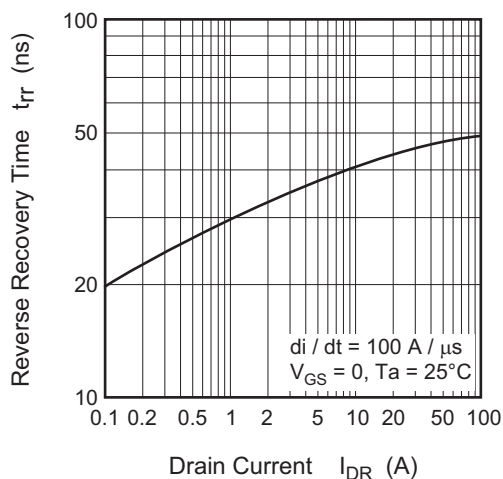
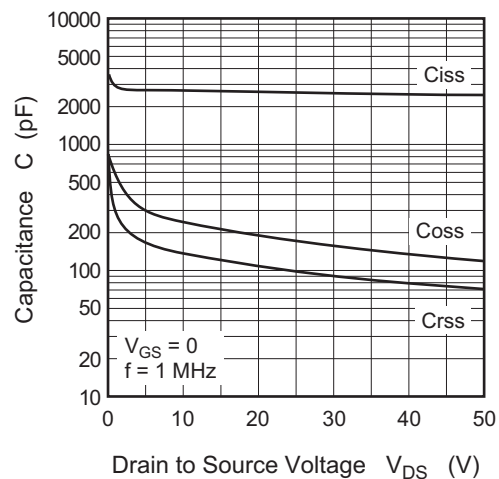


Drain to Source Saturation Voltage vs. Gate to Source Voltage

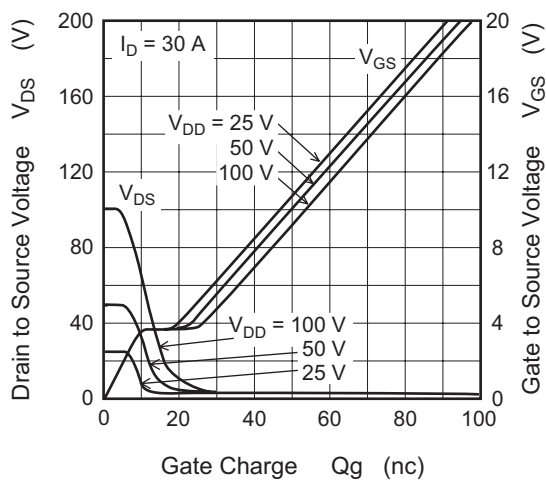


Static Drain to Source on State Resistance vs. Drain Current

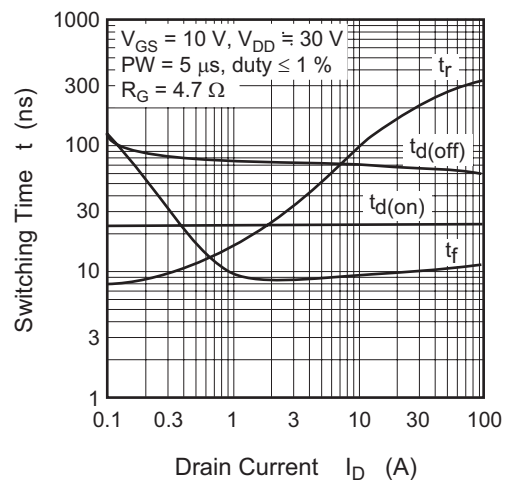


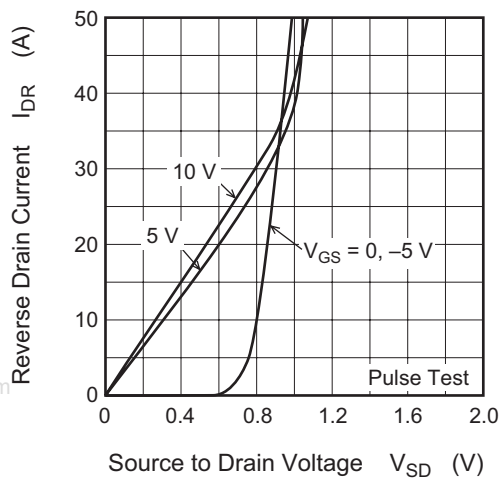
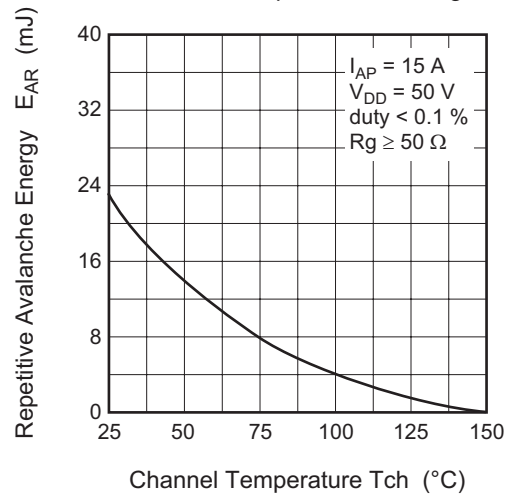
Static Drain to Source on State Resistance  
vs. TemperatureForward Transfer Admittance vs.  
Drain CurrentStatic Drain to Source on State Resistance  
vs. Drain CurrentTypical Capacitance vs.  
Drain to Source Voltage

Dynamic Input Characteristics

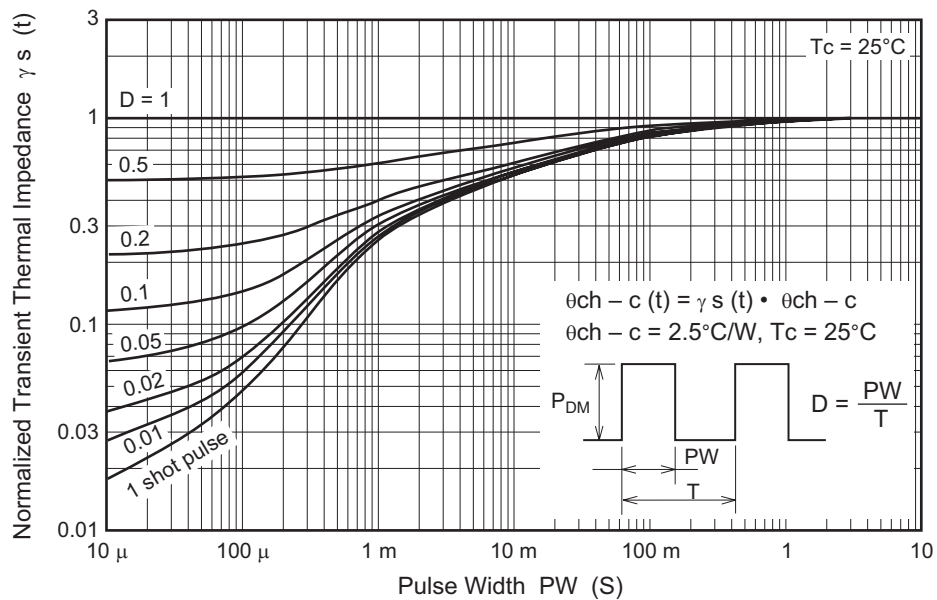


Switching Characteristics

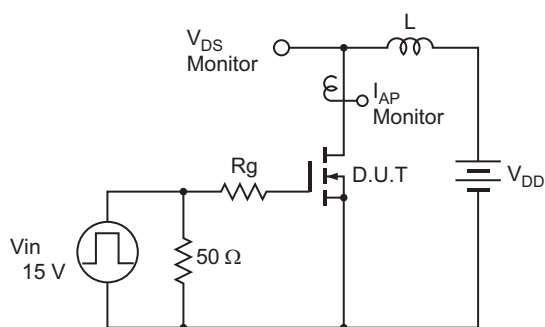


Reverse Drain Current vs.  
Source to Drain VoltageMaximum Avalanche Energy vs.  
Channel Temperature Derating

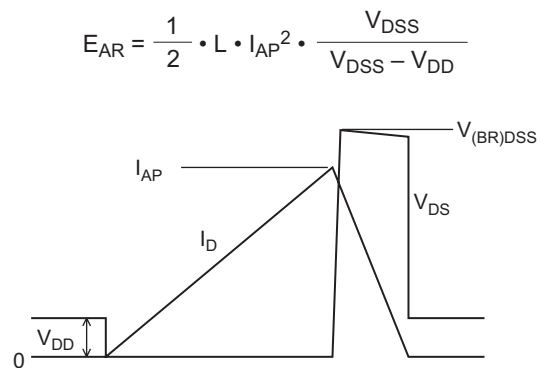
Normalized Transient Thermal Impedance vs. Pulse Width



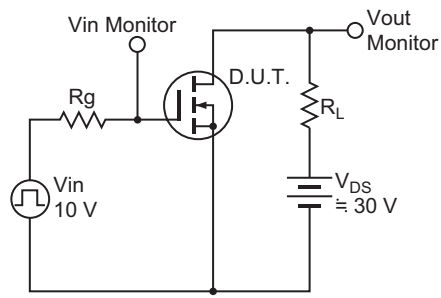
Avalanche Test Circuit



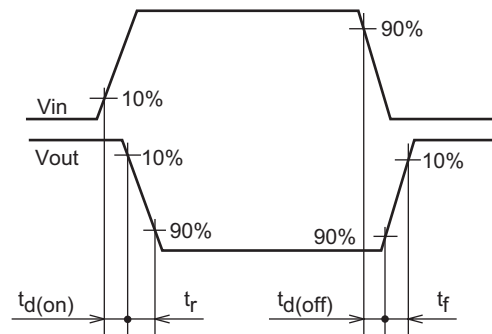
Avalanche Waveform



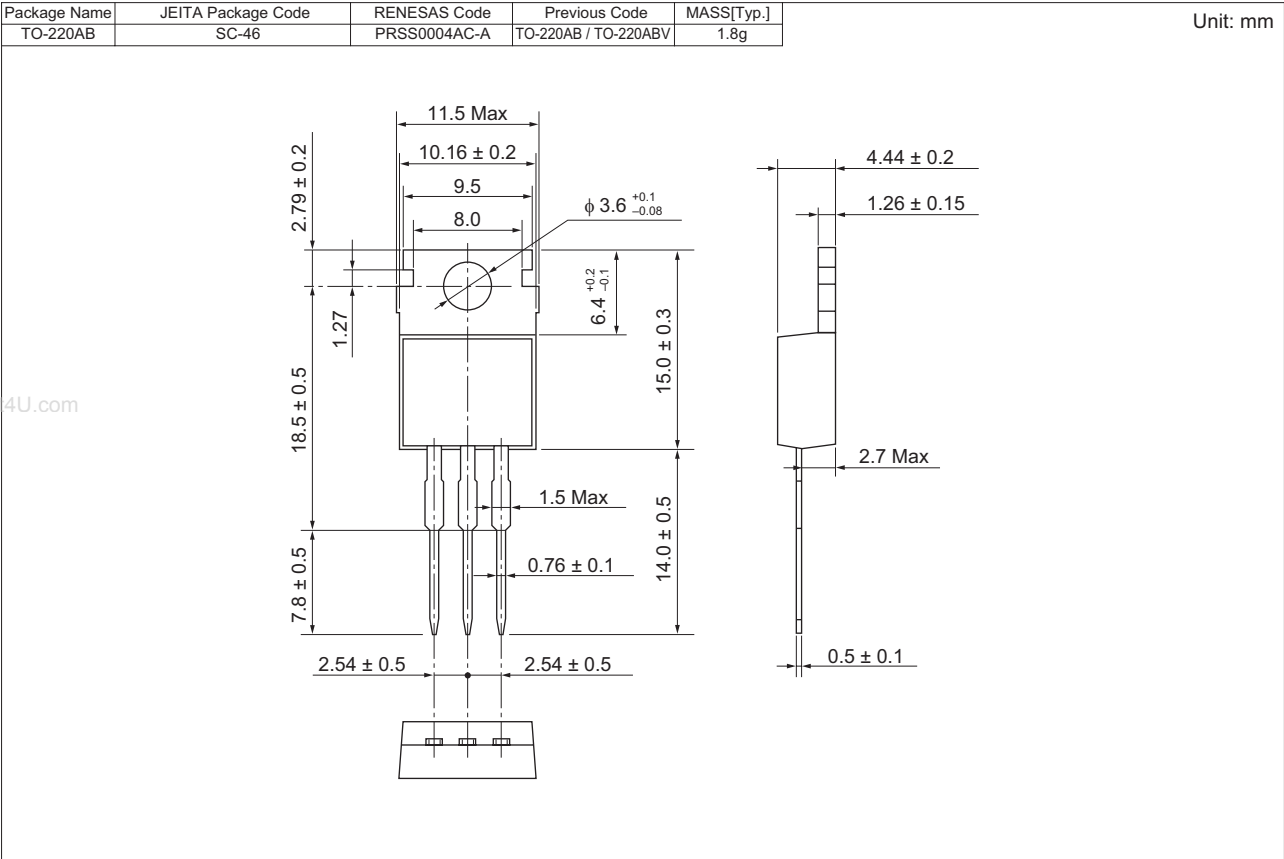
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Notes:

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